



(51) International Patent Classification:

H01L 21/02 (2006.01) *H01L 21/66* (2006.01)
H01L 21/306 (2006.01)

(21) International Application Number:

PCT/US2017/068399

(22) International Filing Date:

26 December 2017 (26.12.2017)

(25) Filing Language:

English

(26) Publication Language:

English

(30) Priority Data:

62/439,334 27 December 2016 (27.12.2016) US

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(81) Designated States (*unless otherwise indicated, for every
kind of national protection available*): AE, AG, AL, AM,
AO, AT, AU, AZ, BA, BB, BG, BH, BN, BR, BW, BY, BZ,
CA, CH, CL, CN, CO, CR, CU, CZ, DE, DJ, DK, DM, DO,
DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN,
HR, HU, ID, IL, IN, IR, IS, JO, JP, KE, KG, KH, KN, KP,
KR, KW, KZ, LA, LC, LK, LR, LS, LU, LY, MA, MD, ME,
MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ,
OM, PA, PE, PG, PH, PL, PT, QA, RO, RS, RU, RW, SA,
SC, SD, SE, SG, SK, SL, SM, ST, SV, SY, TH, TJ, TM, TN,
TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) Designated States (*unless otherwise indicated, for every
kind of regional protection available*): ARIPO (BW, GH,
GM, KE, LR, LS, MW, MZ, NA, RW, SD, SL, ST, SZ, TZ,
UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, RU, TJ,
TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK,

(54) Title: SYSTEMS AND METHODS FOR WETTING SUBSTRATES

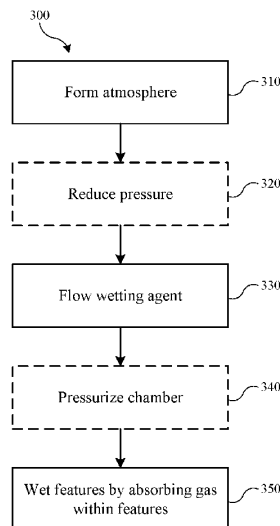


FIG. 3

(57) Abstract: Methods of wetting a semiconductor substrate may include forming a controlled atmosphere in a processing chamber housing the semiconductor substrate. The semiconductor substrate may define a plurality of features, which may include vias. The methods may include flowing a wetting agent into the processing chamber. A chamber pressure may be maintained below about 100 kPa. The methods may also include wetting the plurality of features defined in the substrate.

EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV,
MC, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM,
TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW,
KM, ML, MR, NE, SN, TD, TG).

Published:

- *with international search report (Art. 21(3))*
- *before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments (Rule 48.2(h))*

(88) Date of publication of the international search report:

13 September 2018 (13.09.2018)